

New Jersey Semi-Conductor Products, Inc.

20 STERN AVE.
SPRINGFIELD, NEW JERSEY 07081
U.S.A.

TELEPHONE: (973) 376-2922
(212) 227-6005
FAX: (973) 376-8960

Silicon PNP Power Transistor

2SA1232

DESCRIPTION

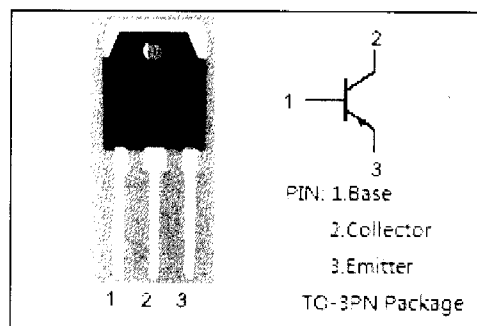
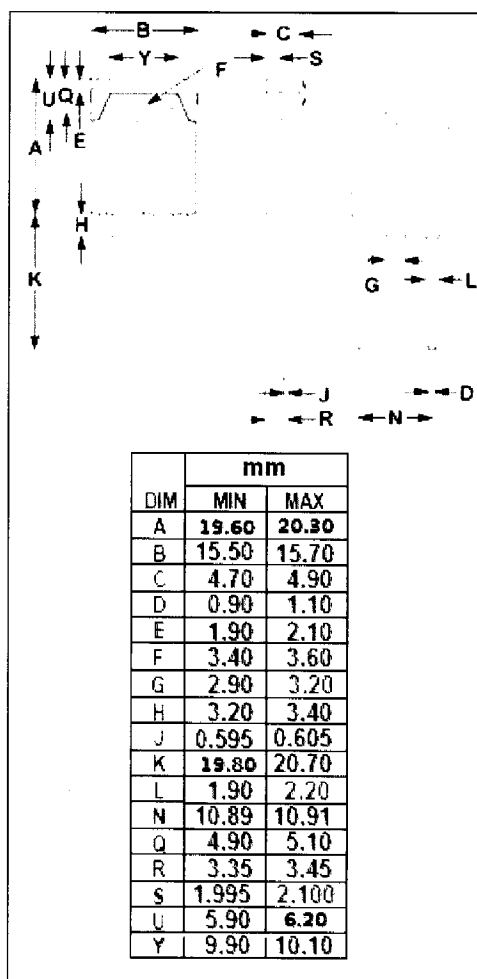
- Collector-Emitter Breakdown Voltage-
: $V_{(BR)CEO} = -130V(\text{Min})$
- Good Linearity of h_{FE}
- Complement to Type 2SC3012

APPLICATIONS

- For audio frequency power amplifier applications.

ABSOLUTE MAXIMUM RATINGS($T_a=25^\circ\text{C}$)

SYMBOL	PARAMETER	VALUE	UNIT
V_{CBO}	Collector-Base Voltage	-130	V
V_{CEO}	Collector-Emitter Voltage	-130	V
V_{EBO}	Emitter-Base Voltage	-5	V
I_C	Collector Current-Continuous	-10	A
I_{CM}	Collector Current-Peak	-15	A
P_C	Collector Power Dissipation @ $T_C=25^\circ\text{C}$	100	W
T_J	Junction Temperature	150	$^\circ\text{C}$
T_{stg}	Storage Temperature Range	-55~150	$^\circ\text{C}$



NJ Semi-Conductors reserves the right to change test conditions, parameter limits and package dimensions without notice. Information furnished by NJ Semi-Conductors is believed to be both accurate and reliable at the time of going to press. However, NJ Semi-Conductors assumes no responsibility for any errors or omissions discovered in its use. NJ Semi-Conductors encourages customers to verify that datasheets are current before placing orders.

Quality Semi-Conductors

Silicon PNP Power Transistor**2SA1232****ELECTRICAL CHARACTERISTICS** $T_C=25^{\circ}\text{C}$ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
$V_{CE(sat)}$	Collector-Emitter Saturation Voltage	$I_C = -5.0\text{A}; I_B = -0.5\text{A}$			-1.5	V
$V_{BE(sat)}$	Base-Emitter Saturation Voltage	$I_C = -5.0\text{A}; I_B = -0.5\text{A}$			-2.0	V
I_{CBO}	Collector Cutoff Current	$V_{CB} = -130\text{V}; I_E = 0$			-50	μA
I_{EBO}	Emitter Cutoff Current	$V_{EB} = -3\text{V}; I_C = 0$			-50	μA
h_{FE-1}	DC Current Gain	$I_C = -2\text{A}; V_{CE} = -5\text{V}$	60		320	
h_{FE-2}	DC Current Gain	$I_C = -5\text{A}; V_{CE} = -5\text{V}$	40			
C_{OB}	Output Capacitance	$I_E = 0; V_{CB} = -10\text{V}; f = 1.0\text{MHz}$		250		pF
f_T	Current-Gain—Bandwidth Product	$I_C = -1\text{A}; V_{CE} = -5\text{V}$		60		MHz

◆ **h_{FE-1} Classifications**

R	Q	P
60-120	100-200	160-320